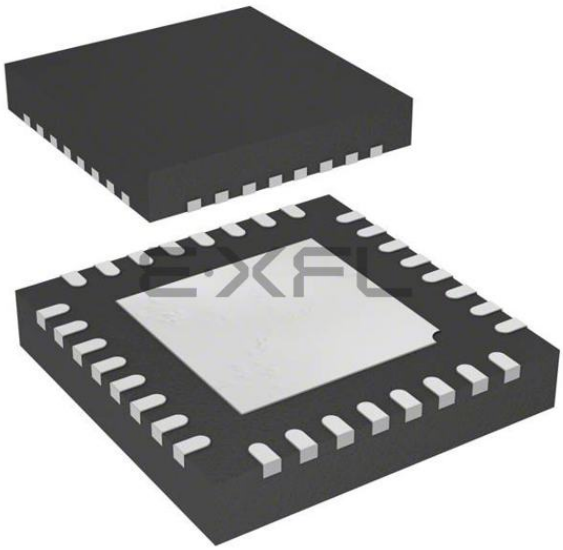

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	27
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f031k6u6

3.16 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

Table 14. STM32F031x4/x6 peripheral register boundary addresses

Bus	Boundary address	Size	Peripheral
	0x4800 1800 - 0x5FFF FFFF	~384 MB	Reserved
AHB2	0x4800 1400 - 0x4800 17FF	1KB	GPIOF
	0x4800 0C00 - 0x4800 13FF	2KB	Reserved
	0x4800 0800 - 0x4800 0BFF	1KB	GPIOC
	0x4800 0400 - 0x4800 07FF	1KB	GPIOB
	0x4800 0000 - 0x4800 03FF	1KB	GPIOA
	0x4002 4400 - 0x47FF FFFF	~128 MB	Reserved
AHB1	0x4002 3400 - 0x4002 3FFF	3 KB	Reserved
	0x4002 3000 - 0x4002 33FF	1 KB	CRC
	0x4002 2400 - 0x4002 2FFF	3 KB	Reserved
	0x4002 2000 - 0x4002 23FF	1 KB	Flash memory interface
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved
	0x4002 1000 - 0x4002 13FF	1 KB	RCC
	0x4002 0400 - 0x4002 0FFF	3 KB	Reserved
	0x4002 0000 - 0x4002 03FF	1 KB	DMA
	0x4001 8000 - 0x4001 FFFF	32 KB	Reserved
APB	0x4001 5C00 - 0x4001 7FFF	9KB	Reserved
	0x4001 5800 - 0x4001 5BFF	1KB	DBGMCU
	0x4001 4C00 - 0x4001 57FF	3KB	Reserved
	0x4001 4800 - 0x4001 4BFF	1KB	TIM17
	0x4001 4400 - 0x4001 47FF	1KB	TIM16
	0x4001 3C00 - 0x4001 43FF	2KB	Reserved
	0x4001 3800 - 0x4001 3BFF	1KB	USART1
	0x4001 3400 - 0x4001 37FF	1KB	Reserved
	0x4001 3000 - 0x4001 33FF	1KB	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	1KB	TIM1
	0x4001 2800 - 0x4001 2BFF	1KB	Reserved
	0x4001 2400 - 0x4001 27FF	1KB	ADC
	0x4001 0800 - 0x4001 23FF	7KB	Reserved
	0x4001 0400 - 0x4001 07FF	1KB	EXTI
	0x4001 0000 - 0x4001 03FF	1KB	SYSCFG
	0x4000 8000 - 0x4000 FFFF	32 KB	Reserved

6.3 Operating conditions

6.3.1 General operating conditions

Table 18. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	48	MHz
f_{PCLK}	Internal APB clock frequency	-	0	48	
V_{DD}	Standard operating voltage	-	2.0	3.6	V
V_{DDA}	Analog operating voltage (ADC not used)	Must have a potential equal to or higher than V_{DD}	V_{DD}	3.6	V
	Analog operating voltage (ADC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.65	3.6	V
V_{IN}	I/O input voltage	TC and RST I/O	–0.3	V_{DDIOx}+0.3	V
		TTa I/O	–0.3	V_{DDA}+0.3(1)	
		FT and FTf I/O	–0.3	5.5(1)	
		BOOT0	0	5.5	
P_D	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	LQFP48	-	364	mW
		UFQFPN32	-	526	
		LQFP32	-	357	
		UFQFPN28	-	169	
		WLCSP25	-	267	
		TSSOP20	-	182	
T_A	Ambient temperature for the suffix 6 version	Maximum power dissipation	–40	85	°C
		Low power dissipation(3)	–40	105	
	Ambient temperature for the suffix 7 version	Maximum power dissipation	–40	105	°C
		Low power dissipation(3)	–40	125	
T_J	Junction temperature range	Suffix 6 version	–40	105	°C
		Suffix 7 version	–40	125	

1. For operation with a voltage higher than V_{DDIOx} + 0.3 V, the internal pull-up resistor must be disabled.
2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax}. See *Section 7.7: Thermal characteristics*.
3. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see *Section 7.7: Thermal characteristics*).

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 19* are derived from tests performed under the ambient temperature condition summarized in *Table 18*.

Table 21. Programmable voltage detector characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD6}	PVD threshold 6	Rising edge	2.66	2.78	2.9	V
		Falling edge	2.56	2.68	2.8	V
V_{PVD7}	PVD threshold 7	Rising edge	2.76	2.88	3	V
		Falling edge	2.66	2.78	2.9	V
$V_{PVDhyst}$(1)	PVD hysteresis	-	-	100	-	mV
$I_{DD(PVD)}$	PVD current consumption	-	-	0.15	0.26(1)	µA

1. Guaranteed by design, not tested in production.

6.3.4 Embedded reference voltage

The parameters given in *Table 22* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*.

Table 22. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.2	1.23	1.25	V
t_{START}	ADC_IN17 buffer startup time	-	-	-	10(1)	µs
$t_{S\_vrefint}$	ADC sampling time when reading the internal reference voltage	-	4(1)	-	-	µs
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	V_{DDA} = 3 V	-	-	10(1)	mV
T_{Coeff}	Temperature coefficient	-	- 100(1)	-	100(1)	ppm/°C

1. Guaranteed by design, not tested in production.

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 13: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Table 25. Typical and maximum current consumption in Stop and Standby modes

Sym-bol	Para-meter	Conditions		Typ @V_{DD} (V_{DD} = V_{DDA})						Max(1)			Unit
				2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Stop mode	Regulator in run mode, all oscillators OFF		15	15.1	15.3	15.5	15.7	16	18(2)	38	55(2)	µA
		Regulator in low-power mode, all oscillators OFF		3.2	3.3	3.4	3.5	3.7	4	5.5(2)	22	41(2)	
	Supply current in Standby mode	LSI ON and IWDG ON		0.8	1.0	1.1	1.2	1.4	1.5	-	-	-	
		LSI OFF and IWDG OFF		0.7	0.8	0.9	1.0	1.1	1.3	2(2)	2.5	3(2)	
I_{DDA}	Supply current in Stop mode	V_{DDA} monitoring ON	Regulator in run mode, all oscillators OFF	1.9	2	2.2	2.3	2.5	2.6	3.5(2)	3.5	4.5(2)	
			Regulator in low-power mode, all oscillators OFF	1.9	2	2.2	2.3	2.5	2.6	3.5(2)	3.5	4.5(2)	
	Supply current in Standby mode		LSI ON and IWDG ON	2.3	2.5	2.7	2.9	3.1	3.3	-	-	-	
			LSI OFF and IWDG OFF	1.8	1.9	2	2.2	2.3	2.5	3.5(2)	3.5	4.5(2)	
	Supply current in Stop mode	V_{DDA} monitoring OFF	Regulator in run mode, all oscillators OFF	1.1	1.2	1.2	1.2	1.3	1.4	-	-	-	
			Regulator in low-power mode, all oscillators OFF	1.1	1.2	1.2	1.2	1.3	1.4	-	-	-	
	Supply current in Standby mode		LSI ON and IWDG ON	1.5	1.6	1.7	1.8	1.9	2.0	-	-	-	
			LSI OFF and IWDG OFF	1	1.0	1.1	1.1	1.2	1.2	-	-	-	

1. Data based on characterization results, not tested in production unless otherwise specified.
2. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

Table 28. Switching output I/O current consumption

Symbol	Parameter	Conditions[1]	I/O toggling frequency (f_{SW})	Typ	Unit
I_{SW}	I/O current consumption	V_{DDIOx} = 3.3 V C =C_{INT}	4 MHz	0.07	mA
			8 MHz	0.15	
			16 MHz	0.31	
			24 MHz	0.53	
			48 MHz	0.92	
		V_{DDIOx} = 3.3 V C_{EXT} = 0 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.18	
			8 MHz	0.37	
			16 MHz	0.76	
			24 MHz	1.39	
			48 MHz	2.188	
		V_{DDIOx} = 3.3 V C_{EXT} = 10 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.32	
			8 MHz	0.64	
			16 MHz	1.25	
			24 MHz	2.23	
			48 MHz	4.442	
		V_{DDIOx} = 3.3 V C_{EXT} = 22 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.49	
			8 MHz	0.94	
			16 MHz	2.38	
			24 MHz	3.99	
		V_{DDIOx} = 3.3 V C_{EXT} = 33 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.64	
			8 MHz	1.25	
			16 MHz	3.24	
			24 MHz	5.02	
		V_{DDIOx} = 3.3 V C_{EXT} = 47 pF C = C_{INT} + C_{EXT}+ C_S C = C_{int}	4 MHz	0.81	
			8 MHz	1.7	
			16 MHz	3.67	
		V_{DDIOx} = 2.4 V C_{EXT} = 47 pF C = C_{INT} + C_{EXT}+ C_S C = C_{int}	4 MHz	0.66	
			8 MHz	1.43	
			16 MHz	2.45	
			24 MHz	4.97	

1. C_S = 7 pF (estimated value).

High-speed internal (HSI) RC oscillator

Table 35. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	8	-	MHz
TRIM	HSI user trimming step	-	-	-	1(2)	%
$DuCy_{(HSI)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI}	Accuracy of the HSI oscillator	T_A = -40 to 105°C	-2.8(3)	-	3.8(3)	%
		T_A = -10 to 85°C	-1.9(3)	-	2.3(3)	
		T_A = 0 to 85°C	-1.9(3)	-	2(3)	
		T_A = 0 to 70°C	-1.3(3)	-	2(3)	
		T_A = 0 to 55°C	-1(3)	-	2(3)	
		T_A = 25°C(4)	-1	-	1	
$t_{su(HSI)}$	HSI oscillator startup time	-	1(2)	-	2(2)	µs
$I_{DDA(HSI)}$	HSI oscillator power consumption	-	-	80	100(2)	µA

1. V_{DDA} = 3.3 V, T_A = -40 to 105°C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Data based on characterization results, not tested in production.
4. Factory calibrated, parts not soldered.

Figure 18. HSI oscillator accuracy characterization results for soldered parts

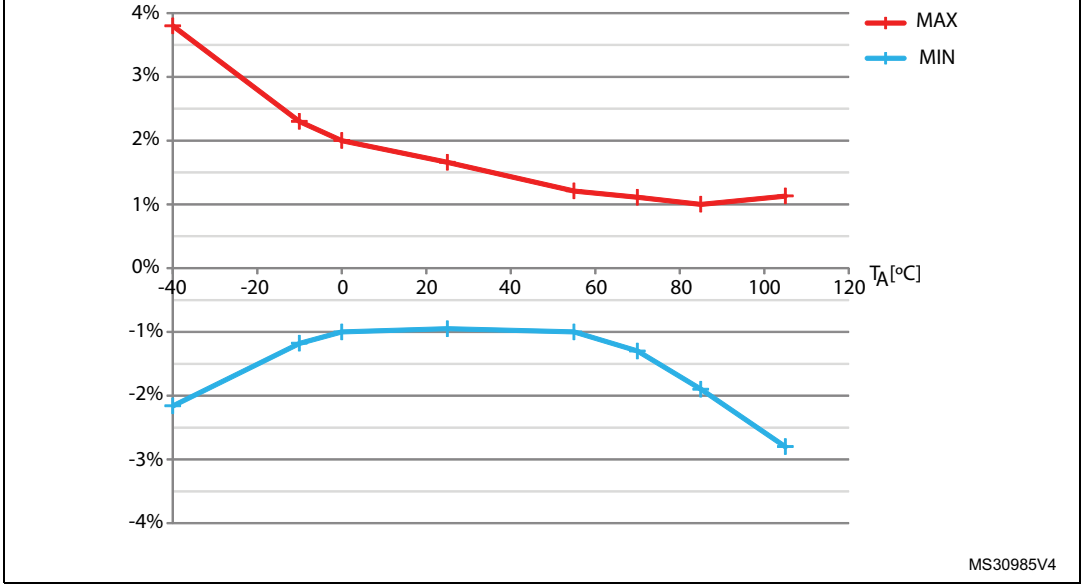


Table 40. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycle
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Year
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycle(2) at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 41*. They are based on the EMS levels and classes defined in application note AN1709.

Table 41. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T_A = +25 °C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T_A = +25°C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Table 45. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	–0	NA	mA
	Injected current on all FT and FTf pins	–5	NA	
	Injected current on all TTa, TC and RESET pins	–5	+5	

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the conditions summarized in *Table 18: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant (except BOOT0).

Table 46. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Low level input voltage	TC and TTa I/O	-	-	0.3 V_{DDIOx}+0.07(1)	V
		FT and FTf I/O	-	-	0.475 V_{DDIOx}–0.2(1)	
		BOOT0	-	-	0.3 V_{DDIOx}–0.3(1)	
		All I/Os except BOOT0 pin	-	-	0.3 V_{DDIOx}	
V_{IH}	High level input voltage	TC and TTa I/O	0.445 V_{DDIOx}+0.398(1)	-	-	V
		FT and FTf I/O	0.5 V_{DDIOx}+0.2(1)	-	-	
		BOOT0	0.2 V_{DDIOx}+0.95(1)	-	-	
		All I/Os except BOOT0 pin	0.7 V_{DDIOx}	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200(1)	-	mV
		FT and FTf I/O	-	100(1)	-	
		BOOT0	-	300(1)	-	
I_{lkg}	Input leakage current(2)	TC, FT and FTf I/O TTa in digital mode $V_{SS} \le V_{IN} \le V_{DDIOx}$	-	-	± 0.1	µA
		TTa in digital mode $V_{DDIOx} \le V_{IN} \le V_{DDA}$	-	-	1	
		TTa in analog mode $V_{SS} \le V_{IN} \le V_{DDA}$	-	-	± 0.2	
		FT and FTf I/O $V_{DDIOx} \le V_{IN} \le 5$ V	-	-	10	

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DDIOx}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 15: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 15: Voltage characteristics*).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 47. Output voltage characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	
V_{OL}	Output low level voltage for an I/O pin	TTL port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		2.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	1.3	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}–1.3	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 6 mA	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	
V_{OLFm+}(3)	Output low level voltage for an FTf I/O pin in Fm+ mode	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
		$\|I_{IO}\|$ = 10 mA	-	0.4	V

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 15: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Data based on characterization results. Not tested in production.

Table 50. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$W_{LATENCY}$(2)(4)	ADC_DR register ready latency	ADC clock = HSI14	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr}(2)	Trigger conversion latency	f_{ADC} = f_{PCLK}/2 = 14 MHz	0.196			µs
		f_{ADC} = f_{PCLK}/2	5.5			1/f_{PCLK}
		f_{ADC} = f_{PCLK}/4 = 12 MHz	0.219			µs
		f_{ADC} = f_{PCLK}/4	10.5			1/f_{PCLK}
		f_{ADC} = f_{HSI14} = 14 MHz	0.179	-	0.250	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	f_{ADC} = f_{HSI14}	-	1	-	1/f_{HSI14}
t_S(2)	Sampling time	f_{ADC} = 14 MHz	0.107	-	17.1	µs
		-	1.5	-	239.5	1/f_{ADC}
t_{STAB}(2)	Stabilization time	-	14			1/f_{ADC}
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 14 MHz, 12-bit resolution	1	-	18	µs
		12-bit resolution	14 to 252 (t_S for sampling +12.5 for successive approximation)			1/f_{ADC}

1. During conversion of the sampled value (12.5 x ADC clock period), an additional consumption of 100 µA on I_{DDA} and 60 µA on I_{DD} should be taken into account.
2. Guaranteed by design, not tested in production.
3. Specified value includes only ADC timing. It does not include the latency of the register access.
4. This parameter specify latency for transfer of the conversion result to the ADC_DR register. EOC flag is set at this time.

Equation 1: R_{AIN} max formula

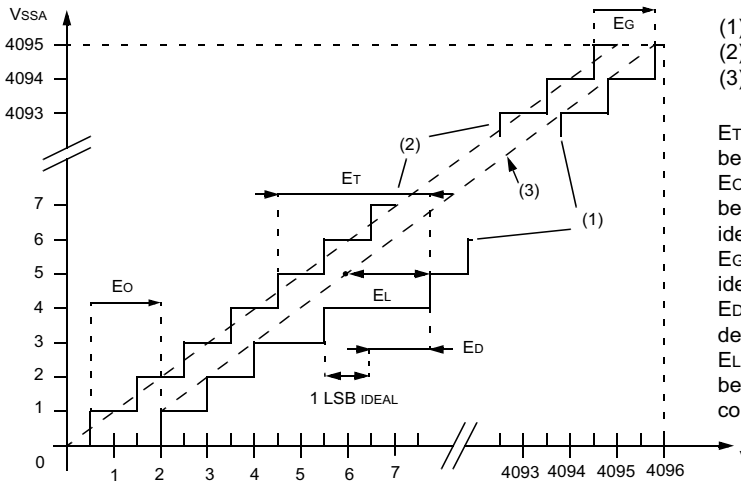
$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 51. R_{AIN} max for f_{ADC} = 14 MHz

T_s (cycles)	t_S (µs)	R_{AIN} max (kΩ)(1)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4

Figure 24. ADC accuracy characteristics



(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

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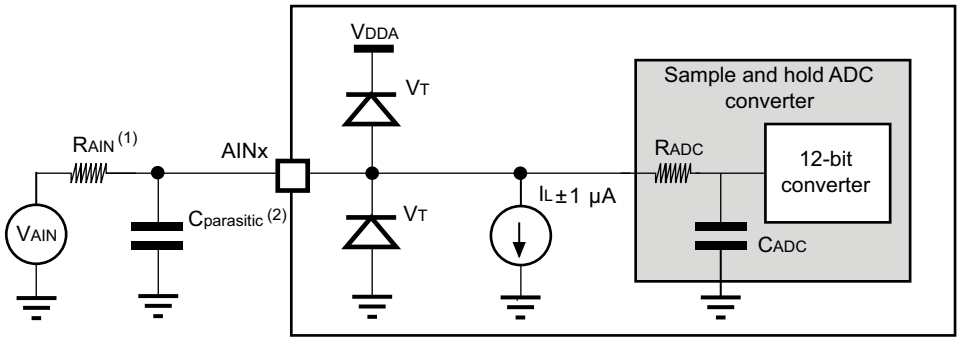
Figure 25. Typical connection diagram using the ADC



MS33900V2

1. Refer to *Table 50: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

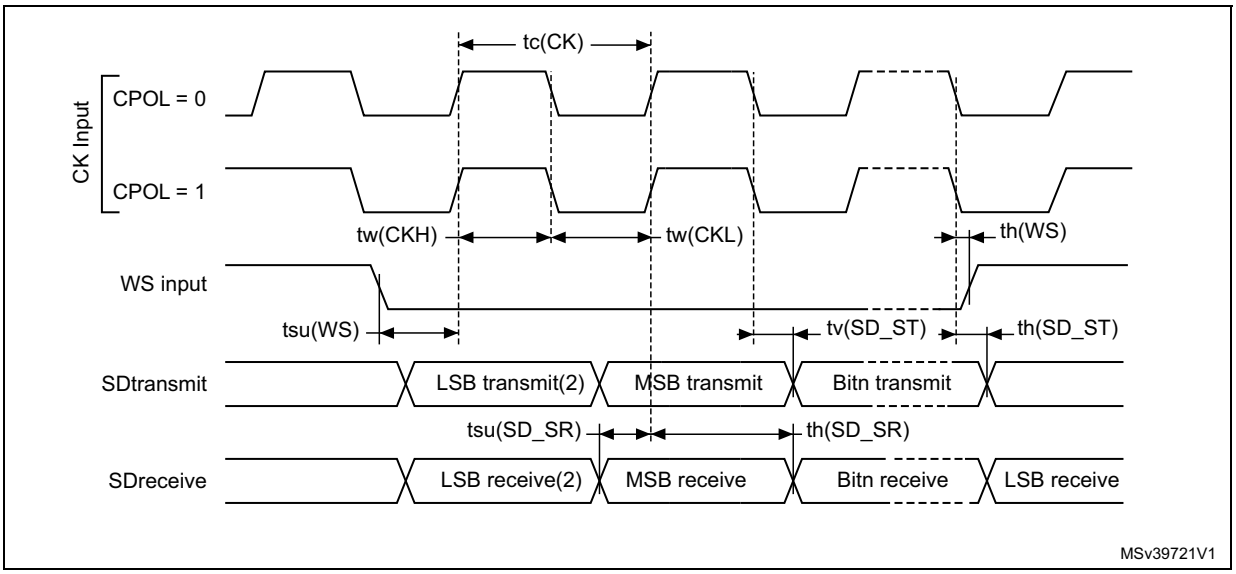
Power supply decoupling should be performed as shown in *Figure 12: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

Table 60. I²S characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	6	-	ns
$t_{su(SD\_SR)}$		Slave receiver	2	-	
$t_{h(SD\_MR)}$(2)	Data input hold time	Master receiver	4	-	
$t_{h(SD\_SR)}$(2)		Slave receiver	0.5	-	
$t_{v(SD\_MT)}$(2)	Data output valid time	Master transmitter	-	4	
$t_{v(SD\_ST)}$(2)		Slave transmitter	-	20	
$t_{h(SD\_MT)}$	Data output hold time	Master transmitter	0	-	
$t_{h(SD\_ST)}$		Slave transmitter	13	-	

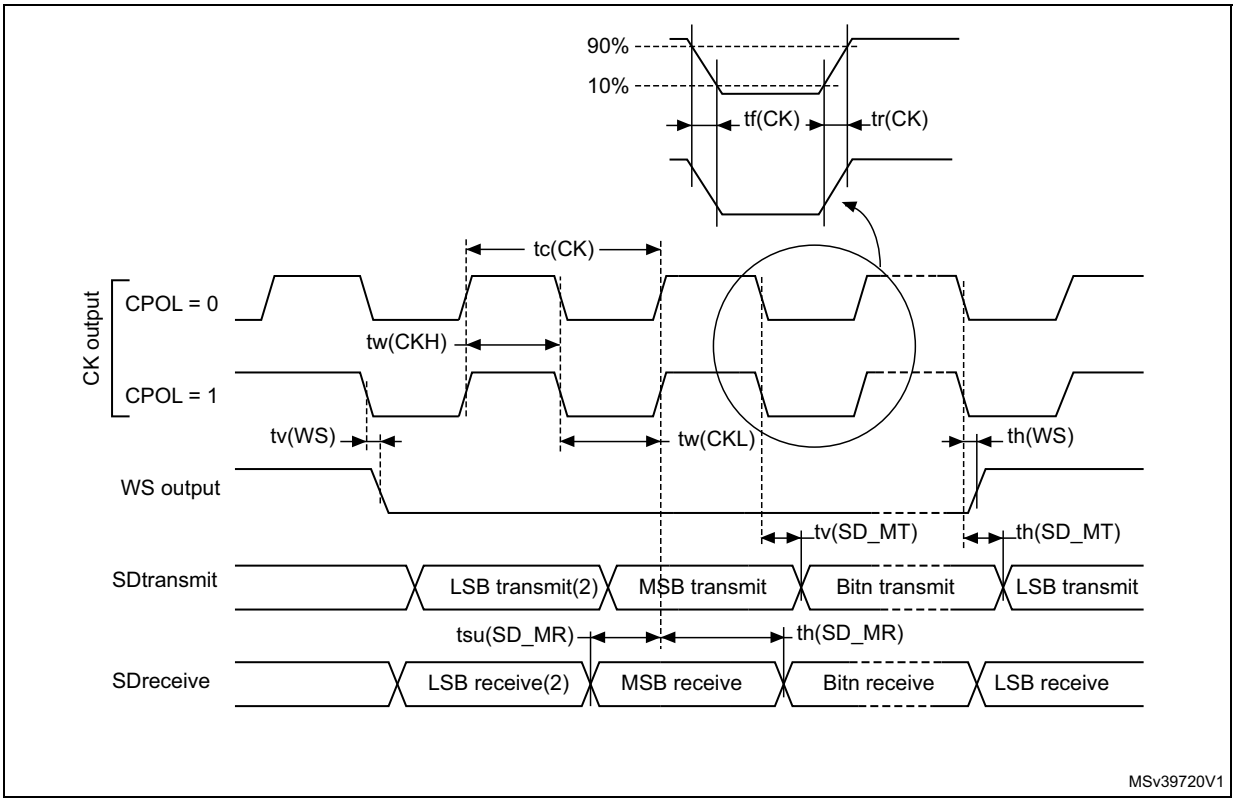
1. Data based on design simulation and/or characterization results, not tested in production.
2. Depends on f_{PCLK}. For example, if f_{PCLK} = 8 MHz, then T_{PCLK} = 1/f_{PLCLK} = 125 ns.

Figure 29. I²S slave timing diagram (Philips protocol)



1. Measurement points are done at CMOS levels: 0.3 × V_{DDIOx} and 0.7 × V_{DDIOx}.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 30. I²S master timing diagram (Philips protocol)



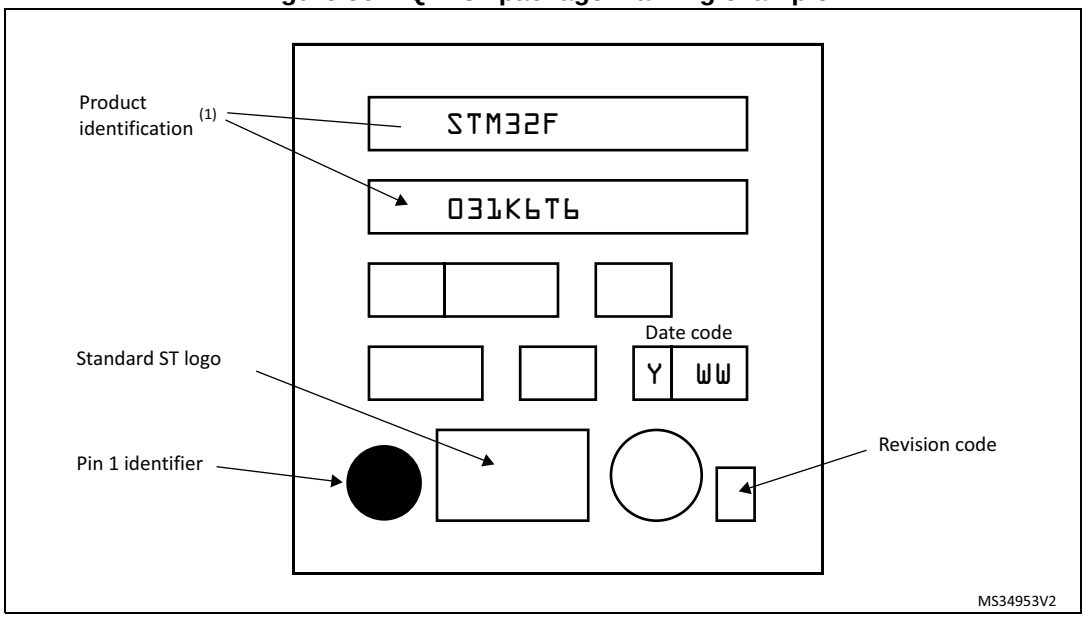
1. Data based on characterization results, not tested in production.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 36. LQFP32 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

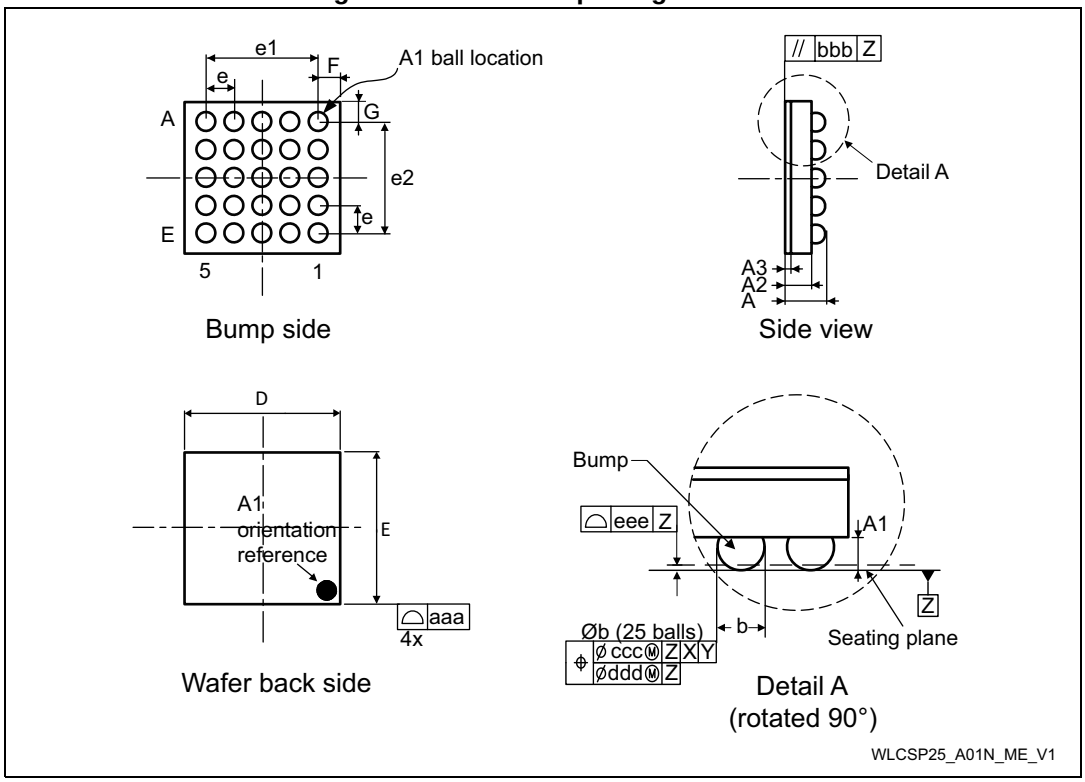
7.3 UFQFPN32 package information

UFQFPN32 is a 32-pin, 5x5 mm, 0.5 mm pitch ultra-thin fine-pitch quad flat package.

7.5 WLCSP25 package information

WLCSP25 is a 25-ball, 2.423 x 2.325 mm, 0.4 mm pitch wafer level chip scale package.

Figure 43. WLCSP25 package outline



1. Drawing is not to scale.

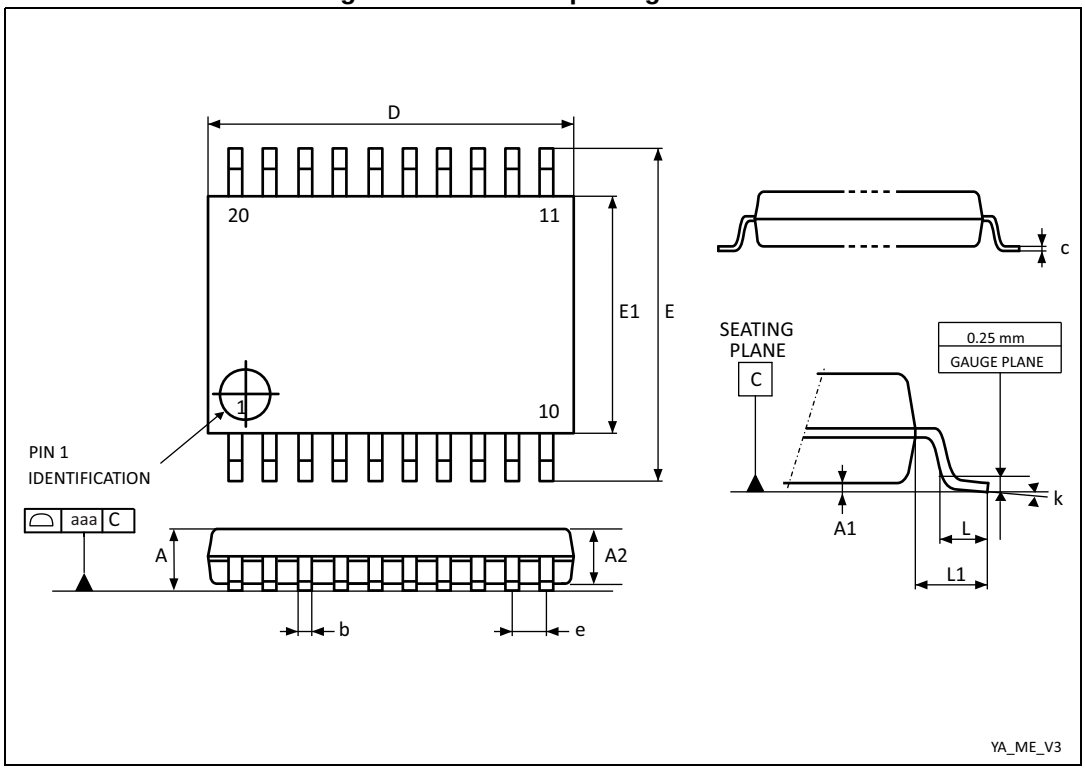
Table 65. WLCSP25 package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3(2)	-	0.025	-	-	0.0010	-
b(3) (4)	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.388	2.423	2.458	0.0940	0.0954	0.0968
E	2.29	2.325	2.36	0.0902	0.0915	0.0929
e	-	0.400	-	-	0.0157	-
e1	-	1.600	-	-	0.0630	-
e2	-	1.600	-	-	0.0630	-
F	-	0.4115	-	-	0.0162	-
G	-	0.3625	-	-	0.0143	-

7.6 TSSOP20 package information

TSSOP20 is a 20-lead thin shrink small-outline, 6.5 x 4.4 mm, 0.65 mm pitch, package.

Figure 46.TSSOP20 package outline



1. Drawing is not to scale.

Table 67. TSSOP20 package mechanical data

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
c	0.090	-	0.200	0.0035	-	0.0079
D[2]	6.400	6.500	6.600	0.2520	0.2559	0.2598
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1[3]	4.300	4.400	4.500	0.1693	0.1732	0.1772
e	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-

7.7.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Ordering information*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F031x4/x6 at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 80 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax} = 175 + 272 = 447 mW

Using the values obtained in *Table 68* T_{Jmax} is calculated as follows:

– For LQFP48, 55 °C/W

T_{Jmax} = 80 °C + (55°C/W × 447 mW) = 80 °C + 24.585 °C = 104.585 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C) see *Table 18: General operating conditions*.

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Section 8: Ordering information*).

Note: With this given P_{Dmax} we can find the TAmax allowed for a given device temperature range (order code suffix 6 or 7).

Suffix 6: T_{Amax} = T_{Jmax} - (55°C/W × 447 mW) = 105-24.585 = 80.415 °C

Suffix 7: T_{Amax} = T_{Jmax} - (55°C/W × 447 mW) = 125-24.585 = 100.415 °C

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Table 70. Document revision history (continued)

Date	Revision	Changes
16-Dec-2015	4 (continued)	– *Section 6.3.16: 12-bit ADC characteristics* - changed introductory sentence – *Table 60: I^2S characteristics*: table reorganized, $t_{v(SD\_ST)}$ max value updated ***Section 7: Package information*:** – *Figure 41: Recommended footprint for UFQFPN28 package* updated ***Section 8: Part numbering*:** – added tray packing to options
06-Jan-2017	5	***Section 6: Electrical characteristics*:** – *Table 34: LSE oscillator characteristics (f_{LSE} = 32.768 kHz)* - information on configuring different drive capabilities removed. See the corresponding reference manual. – *Table 22: Embedded internal reference voltage* - V_{REFINT} values – *Figure 26: SPI timing diagram - slave mode and CPHA = 0* and *Figure 27: SPI timing diagram - slave mode and CPHA = 1* enhanced and corrected ***Section 8: Ordering information*:** – The name of the section changed from the previous “Part numbering”